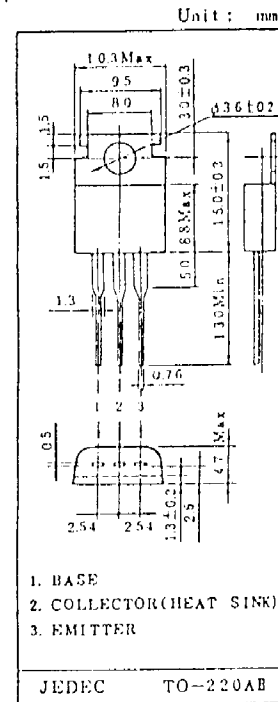


2SC2098

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	70	V
Collector-Emitter Voltage ($R_{EB}=10\Omega$)	V_{CER}	70	V
Emitter-Base Voltage	V_{EBO}	4	V
Collector Current	I_C	6	A
Total Device Dissipation ($T_C=50^\circ\text{C}$)	P_C	20	W
Operating Junction Temperature Range	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cutoff Current	I_{CBO}	$V_{CB}=40V$ $I_E=0$	—	—	0.1	mA
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=1mA$ $I_E=0$	70	—	—	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CER}$	$I_C=10mA$ $R_{EB}=10\Omega$	70	—	—	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=1mA$ $I_C=0$	4	—	—	V
DC Current Gain (Note 1)	h_{FE}	$V_{CE}=5V$ $I_C=4A$	20	—	100	—
Collector-Emitter Saturation Voltage (Note 1)	$V_{CE(sat)}$	$I_C=4A$ $I_B=0.4A$	—	—	1.5	V
Current-Gain-Bandwidth Product	f_T	$V_{CE}=5V$ $I_C=0.5A$	100	—	—	MHz
Output Capacitance	C_{ob}	$V_{CB}=10V$ $I_E=0$ $f=1MHz$	—	80	120	pF

NOTE 1: Pulse Test: Pulse Width $\leq 100\mu s$, Duty Cycle $\leq 3\%$



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